

#### description

The TL1591 is a monolithic integrated sample-and-hold circuit that uses the BiFET process with Schottky-barrier diodes and is designed for use with CCD area imagers. This device consists of an ultra-fast input-buffer amplifier, a digital-controlled diode-bridge switch, and a high-impedance output buffer amplifier. The electronic switch is controlled by an LS-TTL-compatible logic input.

#### functional block diagram





This device contains circuits to protect its inputs and outputs against damage due to high static voltages or electrostatic fields. These circuits have been qualified to protect this device against electrostatic discharges (ESD) of up to 2 kV according to MIL-STD-883C, Method 3015; however, precautions should be taken to avoid application of any voltage higher than maximum-rated voltages to these high-impedance circuits. During storage or handling, the device leads should be shorted together or the device should be placed in

conductive foam. In a circuit, unused inputs should always be connected to an appropriate logic voltage level, preferably either V<sub>CC</sub> or ground. Specific guidelines for handling devices of this type are contained in the publication Guidelines for Handling Electrostatic-Discharge-Sensitive (ESDS) Devices and Assemblies available from Texas Instruments.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



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### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)<sup>†</sup>

Supply voltage, V <sub>CC</sub>	
Input voltage range, V <sub>1</sub>	0 to V <sub>CC</sub>
Continuous total dissipation	See Dissipation Rating Table
Operating free-air temperature range, T <sub>A</sub>	−25°C to 80°C
Storage temperature range, T <sub>STG</sub>	55°C to 150°C

<sup>+</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

#### DISSIPATION RATING TABLE

PACKAGE	T <sub>A</sub> ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T <sub>A</sub> = 25°C	T <sub>A</sub> = 80°C POWER RATING
Р	1000 mW	8.0 mW/°C	560 mW
PS	725 mW	5.8 mW/°C	406 mW

#### recommended operating conditions

	MIN	NOM	MAX	UNIT
Supply voltage, V <sub>CC</sub>	4.75	5	5.5	V
High-level input voltage, V <sub>IH</sub>	2			V
Low-level input voltage, VIL			0.8	V
Peak-to-peak input voltage, VI(PP)			0.8	V
Operating free-air temperature, T <sub>A</sub>	-25		80	°C

# electrical characteristics over ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS		MIN 1	түр‡	MAX	UNIT
VIK	Input clamp voltage					-1.5	V
V <sub>O(PP)</sub>	Peak-to-peak output voltage				1.1		V
ЧΗ	High-level input current	V <sub>CC</sub> = 5.5 V,	V <sub>IH</sub> = 2.7 V			20	μΑ
۱ <sub>IL</sub>	Low-level input current	V <sub>CC</sub> = 5.5 V,	V <sub>IL</sub> = 0.4 V	-	-0.28	-0.4	mA
lo	Output current				0.6		mA
ICC	Supply current	$V_{CC} = 5.5 V$			15	20	mA
r <sub>i</sub>	Input resistance				10		kΩ
r <sub>o</sub>	Output resistance				50		Ω

#### operating characteristics

	PARAMETER	MIN	TYP‡	MAX	UNIT
	Linearity		0.7%	2%	
A <sub>V</sub>	Voltage amplification		0.8	0.9	V/V
	Sample-to-hold offset error		15		mV
	Sample-mode offset error	-150	-50	50	mV
	Hold-mode feedthrough			-50	dB
	Hold-mode droop			100	μV/μs

<sup>‡</sup> All typical values are at  $V_{CC} = 5 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ .



SOCS026B - SEPTEMBER 1989 - REVISED JUNE 1994

## dynamic characteristics (see Figure 1)

PARAMETER	MIN TYP <sup>†</sup>	MAX	UNIT
Acquisition time, 0.6 V to 2%	18		ns
Acquisition time, 0.6 V to 1%	31		ns
Hold-mode settling time	35		ns
Sampling-mode bandwidth	25		MHz
Sampling rate		15	MHz

 $^{\dagger}$  All typical values are at V\_CC = 5 V and T\_A = 25°C.



#### Figure 1. Sample-Hold Definitions

- NOTES: A. Hold-mode settling time is the time from the hold command transistion until the output has settled within a specified error band around the final value.
  - B. Acquisition time is the time required, after the closing of the sampling switch, for the hold capacitor to charge to a full-scale voltage change and then remain within a specified error band around the final value.



SOCS026B - SEPTEMBER 1989 - REVISED JUNE 1994



Figure 2. Test Circuit



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Figure 3. Sample/Hold Accuracy Versus Command Duration



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**MECHANICAL DATA** 

P(R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters). B. This drawing is subject to change without notice.



SOCS026B - SEPTEMBER 1989 - REVISED JUNE 1994

#### **MECHANICAL DATA**

### PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

PS/R-PDSO-G8

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.



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